

## UNITED STATES PATENT AND TRADEMARK OFFICE



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER OF PATENTS AND TRADEMARKS Washington, D.C. 20231 www.nspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/890,120	07/27/2001	Jean-Luc Pelloie	025219-336	5893
75	590 02/18/2003		•	
ROBERT E. KREBS THELEN REID & PRIEST LLP P. O. BOX 640640			EXAMINER	
			ORTIZ, EDGARDO	
SAN JOSE, CA 95164-0640			ART UNIT	PAPER NUMBER
			2815	
			DATE MAILED: 02/18/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

# Office Action Summary

Application No. 09/890,120

Applicant(s)

Pelloie Et.al.

Examiner

**Edgardo Ortiz** 

Art Unit 2815



The MAILING DATE of this communication appears on the cover sheet with the correspondence address							
	for Reply						
THE	A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136 (a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the						
mailing	mailing date of this communication.  If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.						
- If NO p - Failure - Any re	period for reply is specified above, the maximum statutory period will apply to reply within the set or extended period for reply will, by statute, cause t ply received by the Office later than three months after the mailing date of	and will expire SIX (6) Natherlands the application to become	MONTHS from the ABANDO	rom the mailing date of this communication. ONED (35 U.S.C. § 133),			
earned Status	patent term adjustment. See 37 CFR 1.704(b).						
1)[💢	Responsive to communication(s) filed on <u>Dec 18, 2</u>			·			
2a) 🗌	This action is <b>FINAL</b> . 2b) 💢 This ac	ction is non-final.					
3) 🗌	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11; 453 O.G. 213.						
Disposit	tion of Claims						
4) 💢	Claim(s) <u>1-11</u>			is/are pending in the application.			
4	a) Of the above, claim(s)			is/are withdrawn from consideration.			
5) 🗌	Claim(s)			is/are allowed.			
6) 💢	Claim(s) <u>1-11</u>	<del></del>		is/are rejected.			
7) 🗌	Claim(s)			is/are objected to.			
8) 🗆	Claims	ar <b>e</b> :	subject	to restriction and/or election requirement.			
_	Application Papers						
9) $\square$ The specification is objected to by the Examiner.							
10)	The drawing(s) filed on is/are			•			
	Applicant may not request that any objection to the o						
11)∐	The proposed drawing correction filed on			pproved b) $\square$ disapproved by the Examiner.			
If approved, corrected drawings are required in reply to this Office action.							
12) The oath or declaration is objected to by the Examiner.							
	under 35 U.S.C. §§ 119 and 120						
13) Acknowledgement is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).							
	a) ☑ All b) ☐ Some* c) ☐ None of:						
	1. X Certified copies of the priority documents have been received.						
	2. Certified copies of the priority documents have been received in Application No.						
3. X Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  *See the attached detailed Office action for a list of the certified copies not received.							
14) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. § 119(e).							
	a) The translation of the foreign language provisional application has been received.						
15) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.							
Attachment(s)							
1) 💢 Not	ice of References Cited (PTO-892)	4) Interview Sumr	nary (PTO-	413) Paper No(s).			
	ice of Draftsperson's Patent Drawing Review (PTO-948)	5) Notice of Inform	nal Patent	Application (PTO-152)			
3) Note: 13 Information Disclosure Statement(s) (PTO-1449) Paper No(s). 5 6) Other:							

Application/Control Number: 09/890,120

Art Unit: 2815

#### **DETAILED ACTION**

This Office Action is in response to a preliminary amendment filed December 18, 2002 on which Applicant amended claims 1-11.

### Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in-
- (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effect under this subsection of a national application published under section 122(b) only if the international application designating the United States was published under Article 21(2)(a) of such treaty in the English language; or
- (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that a patent shall not be deemed filed in the United States for the purposes of this subsection based on the filing of an international application filed under the treaty defined in section 351(a).

Claims 1, 2, 4, 5 and 6 are rejected under 35 U.S.C. § 102 (e) as being anticipated by Douseki (U.S. Patent No. 5,821,769). With regard to Claim 1, Douseki teaches a MOS transistor (M1) having a gate (23) and a channel (24) of a first conductivity type (p), a first doped zone (25) of a first conductivity type coupled to the channel of said first MOS transistor and a current limiter (M2) coupled between the gate of said MOS transistor and said first doped zone, said current limiter comprising a second doped zone (26) of a second conductivity type (n+) in ohmic contact (30) with said first doped zone. See figure 9A.

Page 3

Application/Control Number: 09/890,120

Art Unit: 2815

With regard to Claim 2, Douseki teaches a current limiter (M2) comprising a second transistor, the second doped zone (26) embodying the source of said second transistor.

With regard to Claim 4, Douseki teaches a second transistor (M2) has a gate (28) coupled to the second doped zone (26).

With regard to Claim 5, Douseki teaches a terminal (B) that is coupled to the gate of the second transistor (M2) and to the second doped zone (26).

With regard to Claim 6, Douseki teaches a drain (27) of the second transistor (M2) that is coupled to the gate (23) of the first MOS transistor (M1).

### Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 3 is rejected under 35 U.S.C. § 103 (a) as being unpatentable over Douseki (U.S. Patent No. 5,821,769) in view of Hu et.al. (International Application WO 96/07205). Douseki, as stated

Page 4

Application/Control Number: 09/890,120

Art Unit: 2815

supra, essentially discloses the claimed invention but fails to show, a gate polarization terminal coupled to the gate of the second transistor. Hu discloses a MOS transistor (32) connected to a second transistor (30) that provides an external bias and which has a gate polarization terminal (gate voltage) coupled to its gate. See Figure 15. Therefore, it would have been an obvious modification to someone with ordinary skill in the art, at the time of the invention, to modify the structure as taught by Douseki to include a gate polarization terminal coupled to the gate of the second transistor, as clearly suggested by Hu, in order to improve the current drive of a MOS transistor.

Claims 7-11 are rejected under 35 U.S.C. § 103 (a) as being unpatentable over Douseki (U.S. Patent No. 5,821,769) in view of Voldman et.al. (U.S. Patent No. 6,015,993). Douseki teaches a current limiter (M2) including a second doped zone (26) embodying a first terminal and a third doped zone (27) embodying a second terminal of the current limiter. See figure 9A.

However, Douseki fails to show that the current limiter comprises a diode wherein the second and third doped zones are of opposite conductivity type. Voldman discloses a FET diode structure including doped zones (140, 144) which embody the terminals of the diode and are of opposite conductivity type. See figure 2. Therefore, it would have been an obvious modification to someone with ordinary skill in the art, at the time of the invention, to modify the structure as taught by Douseki to include current limiter comprising a FET diode structure and doped zones

Application/Control Number: 09/890,120

Page 5

Art Unit: 2815

which embody the terminals of the diode and are of opposite conductivity type, as clearly suggested by Voldman, in order to reduce voltage stress and electro-static discharge.

With regard to Claim 8, Douseki teaches a fourth doped zone (29) disposed between the second (26) and third (27) doped zones, said fourth doped zone having the same conductivity type as the conductivity type of either the second or third zones.

With regard to Claim 9, Douseki teaches a third doped zone (27) coupled to the gate (25) of the first MOS transistor (M1).

With regard to Claim 10, Douseki teaches a gate (28) extending over the fourth doped zone (29).

With regard to Claim 11, Douseki teaches a gate (28) coupled to one of the terminals (26).

#### Conclusion

3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Examiner Edgardo Ortiz (Art Unit 2815), whose telephone number is (703) 308-6183 or by fax at (703) 308-7722. In case the Examiner can not be reached, you might call Supervisor Eddie Lee at (703) 308-1690. Any inquiry of a general nature or relating to the status

Art Unit: 2815

of this application should be directed to the Group 2800 receptionist whose telephone number is (703) 308-0956.

EO/AU 2815

2/6/03

SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800